

MOS FIELD EFFECT TRANSISTOR 2SK3740

SWITCHING N-CHANNEL POWER MOS FET

DESCRIPTION

The 2SK3740 is N-channel MOS FET device that features a low on-state resistance and excellent switching characteristics, designed for high voltage applications such as lamp drive, DC/DC converter, and actuator driver.

FEATURES

- Gate voltage rating: ±30 V
- Low on-state resistance $R_{DS(on)} = 160 \text{ m}\Omega$ MAX. (Vgs = 10 V, Ip = 10 A)
- Low gate charge

 $Q_G = 47 \text{ nC TYP.}$ ($V_{DD} = 200 \text{ V}$, $V_{GS} = 10 \text{ V}$, $I_D = 20 \text{ A}$)

• Surface mount package available

ORDERING INFORMATION

PART NUMBER	PACKAGE
2SK3740-ZK	TO-263 (MP-25ZK)

(TO-263)



ABSOLUTE MAXIMUM RATINGS (TA = 25°C)

Drain to Source Voltage (Vgs = 0 V)	VDSS	250	V
Gate to Source Voltage (Vps = 0 V)	Vgss	±30	V
Drain Current (DC) (Tc = 25°C)	I _{D(DC)}	±20	Α
Drain Current (pulse) Note1	D(pulse)	±60	Α
Total Power Dissipation	P _{T1}	1.5	W
Total Power Dissipation (Tc = 25°C)	P _{T2}	100	W
Channel Temperature	Tch	150	°C
Storage Temperature	Tstg	-55 to +150	°C
Single Avalanche Current Note2	las	20	Α
Single Avalanche Energy Note2	Eas	40	mJ

Notes 1. PW \leq 10 μ s, Duty Cycle \leq 1%

2. Starting T_{ch} = 25°C, V_{DD} = 125 V, R_G = 25 Ω , V_{GS} = 20 \rightarrow 0 V, L = 100 μ H

THERMAL RESISTANCE

Channel to Case Thermal Resistance	Rth(ch-C)	1.25	°C/W
Channel to Ambient Thermal Resistance	Rth(ch-A)	83.3	°C/W

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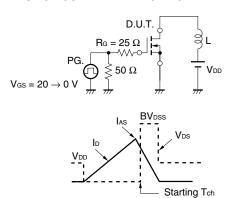


ELECTRICAL CHARACTERISTICS (TA = 25°C)

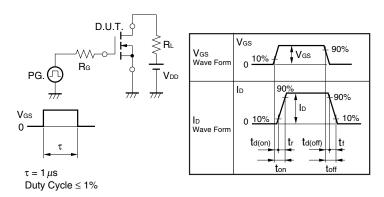
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CHARACTERISTICS	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Zero Gate Voltage Drain Current	IDSS	V _{DS} = 250 V, V _{GS} = 0 V			10	μΑ
Gate Leakage Current	Igss	V _{GS} = ±30 V, V _{DS} = 0 V			±10	μΑ
Gate Cut-off Voltage	V _{GS(off)}	V _{DS} = 10 V, I _D = 1.0 mA	2.5	3.5	4.5	V
Forward Transfer Admittance Note	y _{fs}	V _{DS} = 10 V, I _D = 10 A	7.0	15		S
Drain to Source On-state Resistance Note	RDS(on)	V _{GS} = 10 V, I _D = 10 A		0.12	0.16	Ω
Input Capacitance	Ciss	V _{DS} = 10 V		1720		pF
Output Capacitance	Coss	V _{GS} = 0 V		330		pF
Reverse Transfer Capacitance	Crss	f = 1.0 MHz		170		pF
Turn-on Delay Time	t _{d(on)}	V _{DD} = 125 V, I _D = 10 A		17		ns
Rise Time	t r	V _{GS} = 10 V		17		ns
Turn-off Delay Time	t d(off)	$R_G = 0 \Omega$		49		ns
Fall Time	tf			9		ns
Total Gate Charge	Q _G	V _{DD} = 200 V		47		nC
Gate to Source Charge	Qgs	V _{GS} = 10 V		7		nC
Gate to Drain Charge	Q _{GD}	I _D = 20 A		25		nC
Body Diode Forward Voltage Note	V _F (S-D)	I _F = 20 A, V _{GS} = 0 V		0.91		V
Reverse Recovery Time	trr	I _F = 20 A, V _{GS} = 0 V		210		ns
Reverse Recovery Charge	Qrr	di/dt = 100 A/μs		1.4		μC

Note Pulsed

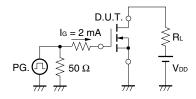
TEST CIRCUIT 1 AVALANCHE CAPABILITY



TEST CIRCUIT 2 SWITCHING TIME



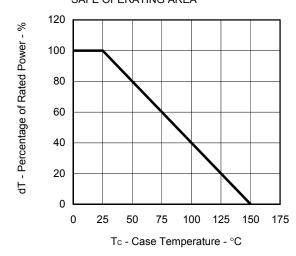
TEST CIRCUIT 3 GATE CHARGE



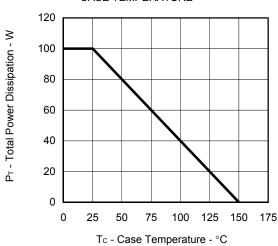


TYPICAL CHARACTERISTICS (TA = 25°C)

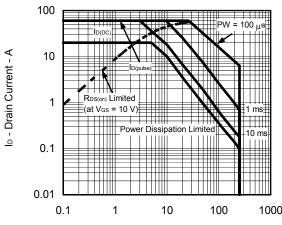
www.DataShee DERATING FACTOR OF FORWARD BIAS SAFE OPERATING AREA

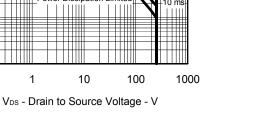


TOTAL POWER DISSIPATION vs. CASE TEMPERATURE

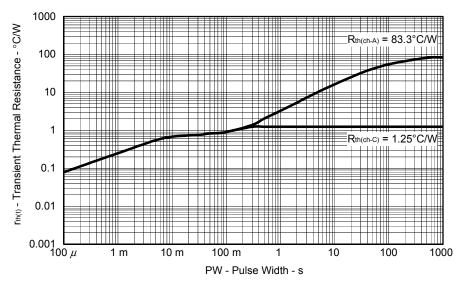


FORWARD BIAS SAFE OPERATING AREA

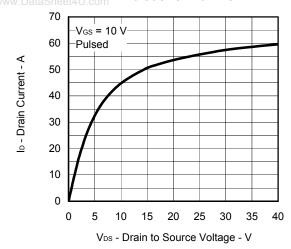




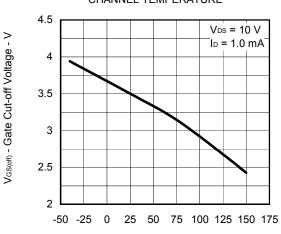
TRANSIENT THERMAL RESISTANCE vs. PULSE WIDTH



DRAIN CURRENT vs. DRAIN TO SOURCE VOLTAGE

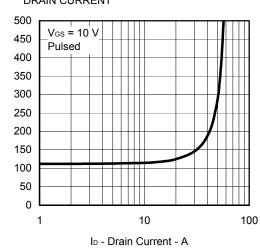


GATE CUT-OFF VOLTAGE vs. CHANNEL TEMPERATURE

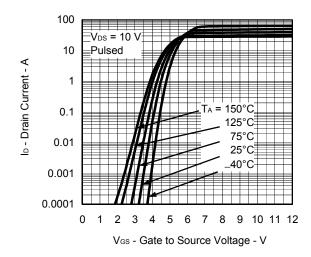


Tch - Channel Temperature - °C

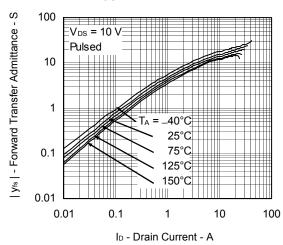
DRAIN TO SOURCE ON-STATE RESISTANCE vs. DRAIN CURRENT



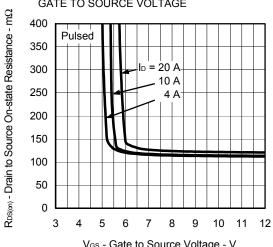
FORWARD TRANSFER CHARACTERISTICS



FORWARD TRANSFER ADMITTANCE vs. DRAIN CURRENT



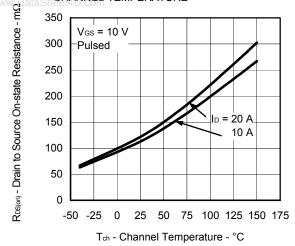
DRAIN TO SOURCE ON-STATE RESISTANCE vs. GATE TO SOURCE VOLTAGE



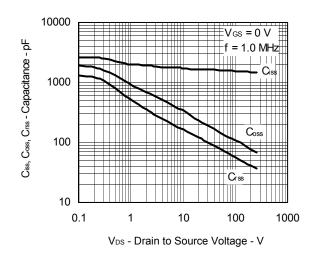
Vgs - Gate to Source Voltage - V

RDS(m) - Drain to Source On-state Resistance - m\Omega

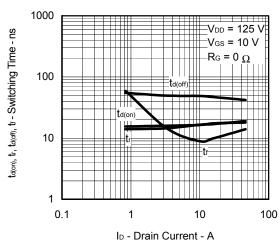
DRAIN TO SOURCE ON-STATE RESISTANCE vs. CHANNEL TEMPERATURE



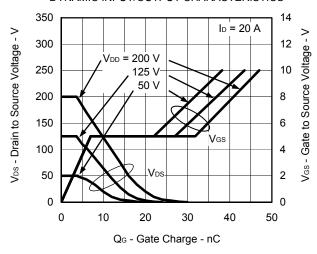
CAPACITANCE vs. DRAIN TO SOURCE VOLTAGE



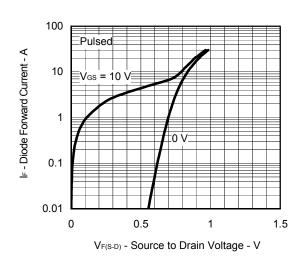
SWITCHING CHARACTERISTICS



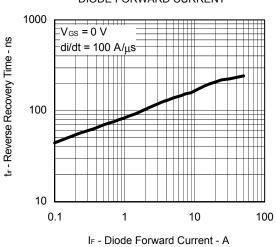
DYNAMIC INPUT/OUTPUT CHARACTERISTICS



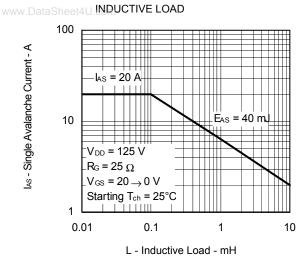
SOURCE TO DRAIN DIODE FORWARD VOLTAGE



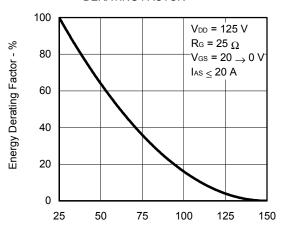
REVERSE RECOVERY TIME vs. DIODE FORWARD CURRENT



SINGLE AVALANCHE CURRENT vs.



SINGLE AVALANCHE ENERGY DERATING FACTOR

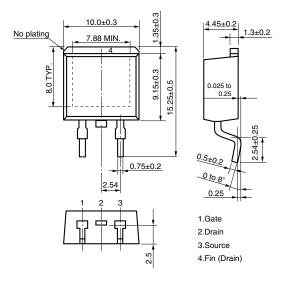


Starting Tch - Starting Channel Temperature - °C

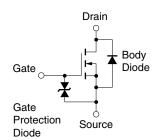
PACKAGE DRAWING (Unit: mm)

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TO-263 (MP-25ZK)



EQUIVALENT CIRCUIT



Remark The diode connected between the gate and source of the transistor serves as a protector against ESD.

When this device actually used, an additional protection circuit is externally required if a voltage exceeding the rated voltage may be applied to this device.

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